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Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I ² C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, I ² S, POR, PWM, WDT
Number of I/O	86
Program Memory Size	384KB (384K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 17x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f302vdt6

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Figure 6. STM32F302xD/E LQFP144 pinout

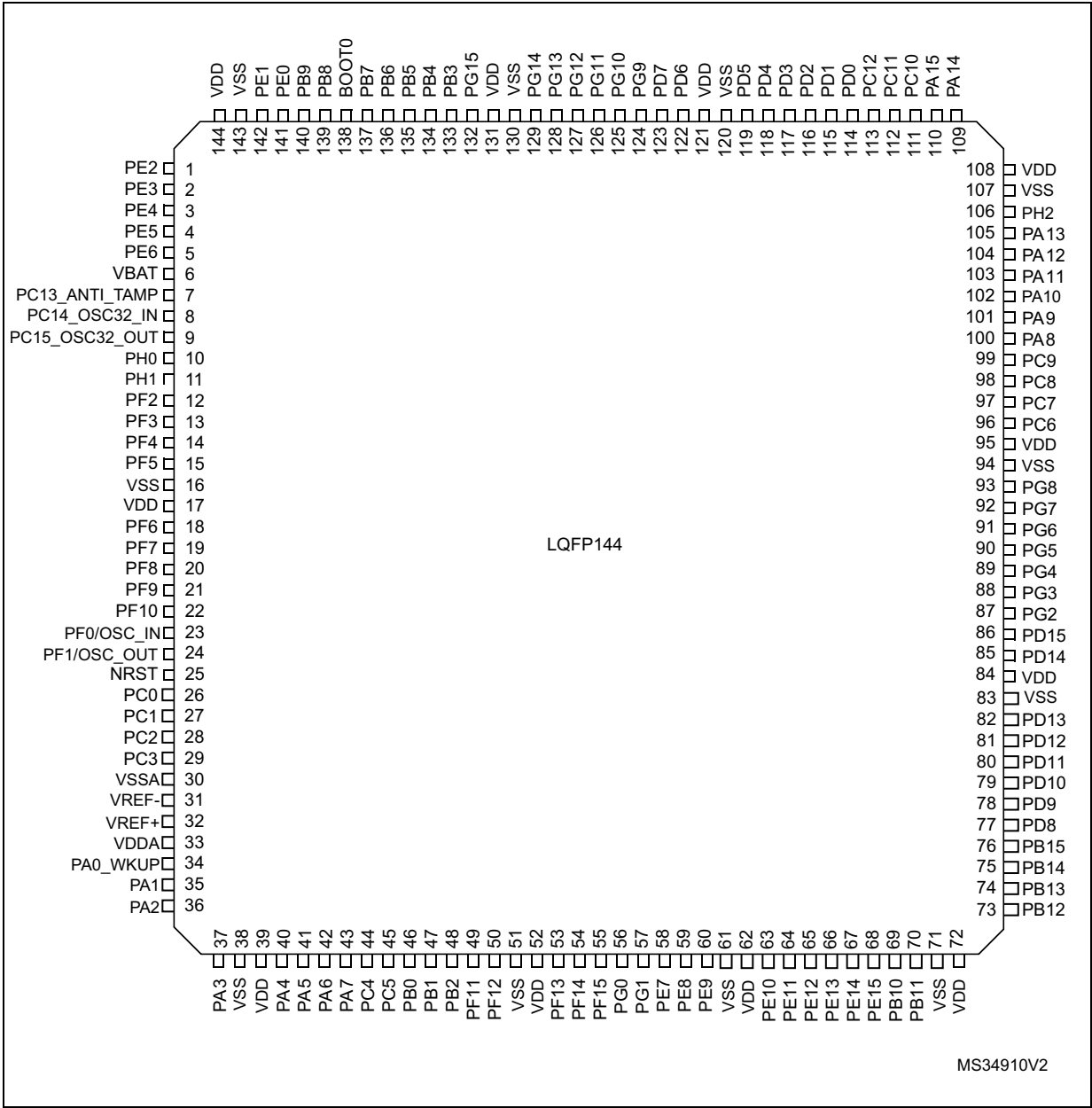


Table 13. STM32F302xD/E pin definitions (continued)

Pin number				Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP64	LQFP100	WLCSP100	LQFP144						
9	16	G9	27	PC1	I/O	TTa	-	EVENTOUT, TIM1_CH2	ADC12_IN7
10	17	G8	28	PC2	I/O	TTa	-	EVENTOUT, TIM1_CH3	ADC12_IN8
11	18	H10	29	PC3	I/O	TTa	-	EVENTOUT, TIM1_CH4, TIM1_BKIN2	ADC12_IN9
12	20	H8	30	VSSA	S	-	(1)	-	-
-	-	-	31	VREF-	S	-	(1)	-	-
-	21	J8	32	VREF+ ⁽⁴⁾	S	-	-	-	-
13	22	J10	33	VDDA	S	-	-	-	-
14	23	H9	34	PA0	I/O	TTa	-	TIM2_CH1/TIM2_ETR, TSC_G1_IO1, USART2_CTS, COMP1_OUT, EVENTOUT	ADC1_IN1 ⁽³⁾ , COMP1_INM, RTC_TAMP2, WKUP1
15	24	J9	35	PA1	I/O	TTa	-	RTC_REFIN, TIM2_CH2, TSC_G1_IO2, USART2_RTS, TIM15_CH1N, EVENTOUT	ADC1_IN2 ⁽³⁾ , COMP1_INP, OPAMP1_VINP
16	25	F7	36	PA2	I/O	TTa	(5)	TIM2_CH3, TSC_G1_IO3, USART2_TX, COMP2_OUT, TIM15_CH1, EVENTOUT	ADC1_IN3 ⁽³⁾ , COMP2_INM, OPAMP1_VOUT
17	26	G7	37	PA3	I/O	TTa	-	TIM2_CH4, TSC_G1_IO4, USART2_RX, TIM15_CH2, EVENTOUT	ADC1_IN4 ⁽³⁾ , OPAMP1_VINM/ OPAMP1_VINP
18	27	K9, K10	38	VSS	S	-	-	-	-
19	28	K8	39	VDD	S	-	(1)	-	-
20	29	J7	40	PA4	I/O	TTa	(5)	TIM3_CH2, TSC_G2_IO1, SPI1_NSS, SPI3_NSS/I2S3_WS, USART2_CK, EVENTOUT	ADC2_IN1 ⁽³⁾ , DAC1_OUT1, COMP1_INM, COMP2_INM, COMP4_INM, COMP6_INM,

Table 13. STM32F302xD/E pin definitions (continued)

Pin number				Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP64	LQFP100	WLCSP100	LQFP144						
-	-	-	90	PG5	I/O	FT	(1)	EVENTOUT, FMC_A15	-
-	-	-	91	PG6	I/O	FT	(1)	EVENTOUT, FMC_INT2	-
-	-	-	92	PG7	I/O	FT	(1)	EVENTOUT, FMC_INT3	-
-	-	-	93	PG8	I/O	FT	(1)	EVENTOUT	-
-	-	-	94	VSS	S	-	(1)	-	-
-	-	-	95	VDD	S	-	(1)	-	-
37	63	F4	96	PC6	I/O	FT	-	EVENTOUT, TIM3_CH1, I2S2_MCK, COMP6_OUT	-
38	64	F2	97	PC7	I/O	FT	-	EVENTOUT, TIM3_CH2, I2S3_MCK	-
39	65	F1	98	PC8	I/O	FT	-	EVENTOUT, TIM3_CH3	-
40	66	F3	99	PC9	I/O	FTf	-	EVENTOUT, TIM3_CH4, I2C3_SDA, I2SCKIN	-
41	67	F5	100	PA8	I/O	FTf	-	MCO, I2C3_SCL, I2C2_SMBAL, I2S2_MCK, TIM1_CH1, USART1_CK, TIM4_ETR, EVENTOUT	-
42	68	E5	101	PA9	I/O	FTf	-	I2C3_SMBAL, TSC_G4_IO1, I2C2_SCL, I2S3_MCK, TIM1_CH2, USART1_TX, TIM15_BKIN, TIM2_CH3, EVENTOUT	-
43	69	E1	102	PA10	I/O	FTf	-	TIM17_BKIN, TSC_G4_IO2, I2C2_SDA, SPI2_MISO/I2S2ext_SD, TIM1_CH3, USART1_RX, COMP6_OUT, TIM2_CH4, EVENTOUT	-
44	70	E2	103	PA11	I/O	FT	-	SPI2_MOSI/I2S2_SD, TIM1_CH1N, USART1_CTS, COMP1_OUT, CAN_RX, TIM4_CH1, TIM1_CH4, TIM1_BKIN2, EVENTOUT	USB_DM

Table 14. STM32F302xD/E alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS_AF	TIM2/15/ 16/17/E VENT	I2C3/TIM1 /2/3/4/8/20 /15/GPCO MP1	I2C3//15/ TSC	I2C1/2/TI M1/8/16/ 17	SPI1/SPI2 /I2S2/SPI3 /I2S3/SPI4 /UART4/5/ Infrared	SPI2/I2S2/ SPI3/I2S3/ TIM1/8/20/ Infrared	USART1/2 /3/CAN/GP COMP6	I2C3/GPC OMP1/2/3/ 4/5/6	CAN/TIM1 /8/15	TIM2/3/ 4/8/17	TIM1/8	FSMC /TIM1	-	-	EVENT
Port G	PG5	-	EVENT OUT	-	-	-	-	-	-	-	-	-	-	FMC_ A15	-	-	-
	PG6	-	EVENT OUT	-	-	-	-	-	-	-	-	-	-	FMC_ INT2	-	-	-
	PG7	-	EVENT OUT	-	-	-	-	-	-	-	-	-	-	FMC_ INT3	-	-	-
	PG8	-	EVENT OUT	-	-	-	-	-	-	-	-	-	-	-	-	-	-
	PG9	-	EVENT OUT	-	-	-	-	-	-	-	-	-	-	FMC_NE 2/FMC_ NCE3	-	-	-
	PG10	-	EVENT OUT	-	-	-	-	-	-	-	-	-	-	FMC_ NCE4_1/ FMC_ NE3	-	-	-
	PG11	-	EVENT OUT	-	-	-	-	-	-	-	-	-	-	FMC_ NCE4_2	-	-	-
	PG12	-	EVENT OUT	-	-	-	-	-	-	-	-	-	-	FMC_ NE4	-	-	-
	PG13	-	EVENT OUT	-	-	-	-	-	-	-	-	-	-	FMC_ A24	-	-	-
	PG14	-	EVENT OUT	-	-	-	-	-	-	-	-	-	-	FMC_ A25	-	-	-
	PG15	-	EVENT OUT	-	-	-	-	-	-	-	-	-	-	-	-	-	-

5 Memory mapping

Figure 9. STM32F302xD/E memory map

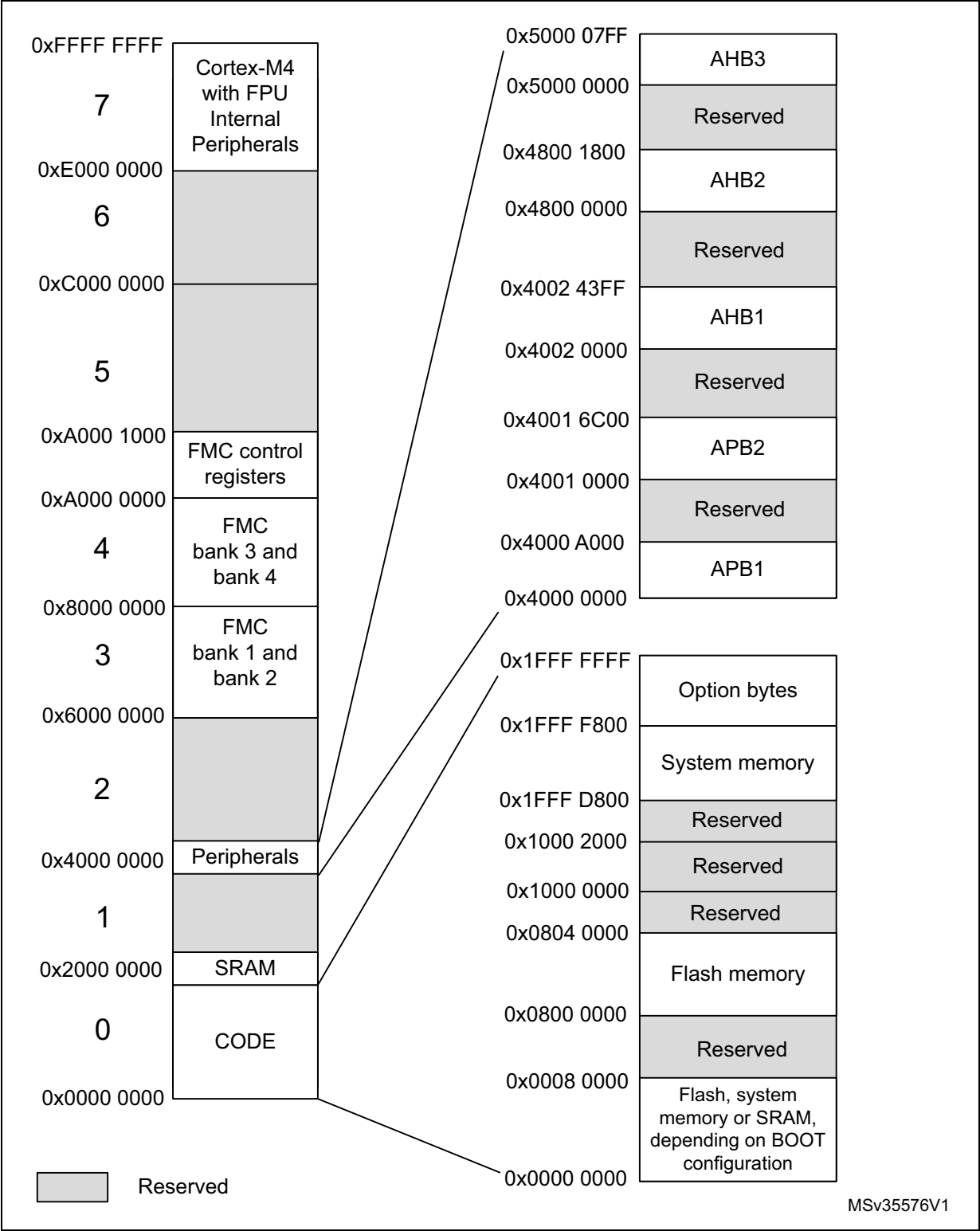


Table 15. Memory map, peripheral register boundary addresses (continued)

Bus	Boundary address	Size (bytes)	Peripheral
APB2	0x4001 2C00 - 0x4001 2FFF	1 K	TIM1
	0x4001 0800 - 0x4001 2BFF	9 K	Reserved
	0x4001 0400 - 0x4001 07FF	1 K	EXTI
	0x4001 0000 - 0x4001 03FF	1 K	SYSCFG + COMP + OPAMP
-	0x4000 7C00 - 0x4000 FFFF	32 K	Reserved
APB1	0x4000 7800 - 0x4000 7BFF	1 K	I2C3
	0x4000 7400 - 0x4000 77FF	1 K	DAC
	0x4000 7000 - 0x4000 73FF	1 K	PWR
	0x4000 6800 - 0x4000 6FFF	2 K	Reserved
	0x4000 6400 - 0x4000 67FF	1 K	bxCAN
	0x4000 6000 - 0x4000 63FF	1 K	USB/CAN SRAM
	0x4000 5C00 - 0x4000 5FFF	1 K	USB device FS
	0x4000 5800 - 0x4000 5BFF	1 K	I2C2
	0x4000 5400 - 0x4000 57FF	1 K	I2C1
	0x4000 5000 - 0x4000 53FF	1 K	UART5
	0x4000 4C00 - 0x4000 4FFF	1 K	UART4
	0x4000 4800 - 0x4000 4BFF	1 K	USART3
	0x4000 4400 - 0x4000 47FF	1 K	USART2
	0x4000 4000 - 0x4000 43FF	1 K	I2S3ext
	0x4000 3C00 - 0x4000 3FFF	1 K	SPI3/I2S3
	0x4000 3800 - 0x4000 3BFF	1 K	SPI2/I2S2
	0x4000 3400 - 0x4000 37FF	1 K	I2S2ext
	0x4000 3000 - 0x4000 33FF	1 K	IWDG
	0x4000 2C00 - 0x4000 2FFF	1 K	WWDG
	0x4000 2800 - 0x4000 2BFF	1 K	RTC
	0x4000 1800 - 0x4000 27FF	4 K	Reserved
	0x4000 1000 - 0x4000 13FF	1 K	TIM6
	0x4000 0C00 - 0x4000 0FFF	1 K	Reserved
	0x4000 0800 - 0x4000 0BFF	1 K	TIM4
	0x4000 0400 - 0x4000 07FF	1 K	TIM3
	0x4000 0000 - 0x4000 03FF	1 K	TIM2

6.3.2 Operating conditions at power-up / power-down

The parameters given in [Table 20](#) are derived from tests performed under the ambient temperature condition summarized in [Table 19](#).

Table 20. Operating conditions at power-up / power-down

Symbol	Parameter	Conditions	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	-	0	∞	$\mu\text{s/V}$
	V_{DD} fall time rate		20	∞	
t_{VDDA}	V_{DDA} rise time rate	-	0	∞	
	V_{DDA} fall time rate		20	∞	

6.3.3 Embedded reset and power control block characteristics

The parameters given in [Table 21](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 19](#).

Table 21. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$V_{POR/PDR}^{(1)}$	Power on/power down reset threshold	Falling edge	1.8 ⁽²⁾	1.88	1.96	V
		Rising edge	1.84	1.92	2.0	V
$V_{PDRhyst}^{(1)}$	PDR hysteresis	-	-	40	-	mV

1. The PDR detector monitors V_{DD} and also V_{DDA} (if kept enabled in the option bytes). The POR detector monitors only V_{DD} .
2. The product behavior is guaranteed by design down to the minimum $V_{POR/PDR}$ value.

Table 22. Programmable voltage detector characteristics

Symbol	Parameter	Conditions	Min ⁽¹⁾	Typ	Max ⁽¹⁾	Unit
V_{PVD0}	PVD threshold 0	Rising edge	2.1	2.18	2.26	V
		Falling edge	2	2.08	2.16	
V_{PVD1}	PVD threshold 1	Rising edge	2.19	2.28	2.37	
		Falling edge	2.09	2.18	2.27	
V_{PVD2}	PVD threshold 2	Rising edge	2.28	2.38	2.48	
		Falling edge	2.18	2.28	2.38	
V_{PVD3}	PVD threshold 3	Rising edge	2.38	2.48	2.58	
		Falling edge	2.28	2.38	2.48	
V_{PVD4}	PVD threshold 4	Rising edge	2.47	2.58	2.69	
		Falling edge	2.37	2.48	2.59	
V_{PVD5}	PVD threshold 5	Rising edge	2.57	2.68	2.79	
		Falling edge	2.47	2.58	2.69	

On-chip peripheral current consumption

The MCU is placed under the following conditions:

- all I/O pins are in analog input configuration
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
 - with all peripherals clocked off
 - with only one peripheral clocked on
- ambient operating temperature at 25°C and $V_{DD} = V_{DDA} = 3.3\text{ V}$.

Table 33. Peripheral current consumption

Peripheral	Typical consumption ⁽¹⁾	Unit
	I_{DD}	
BusMatrix ⁽²⁾	8.3	μA/MHz
DMA1	7.0	
DMA2	5.4	
FSMC	35.0	
CRC	1.5	
GPIOH	1.3	
GPIOA	5.4	
GPIOB	5.3	
GPIOC	5.4	
GIOD	5.0	
GPIOE	5.4	
GPIOF	5.2	
GPIOG	5.0	
TSC	5.2	
ADC1&2	15.4	
APB2-Bridge ⁽³⁾	3.1	
SYSCFG	4.0	
TIM1	26.0	
USART1	17.7	
SPI4	6.2	
TIM15	11.9	
TIM16	8.0	
TIM17	8.5	

6.3.10 Memory characteristics

Flash memory

The characteristics are given at $T_A = -40$ to $105\text{ }^{\circ}\text{C}$ unless otherwise specified.

Table 43. Flash memory characteristics

Symbol	Parameter	Conditions	Min	Typ	Max ⁽¹⁾	Unit
t_{prog}	16-bit programming time	$T_A = -40$ to $+105\text{ }^{\circ}\text{C}$	40	53.5	60	μs
t_{ERASE}	Page (2 KB) erase time	$T_A = -40$ to $+105\text{ }^{\circ}\text{C}$	20	-	40	ms
t_{ME}	Mass erase time	$T_A = -40$ to $+105\text{ }^{\circ}\text{C}$	20	-	40	ms
I_{DD}	Supply current	Write mode	-	-	10	mA
		Erase mode	-	-	12	mA

1. Guaranteed by design, not tested in production.

Table 44. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Value	Unit
			Min ⁽¹⁾	
N_{END}	Endurance	$T_A = -40$ to $+85\text{ }^{\circ}\text{C}$ (6 suffix versions) $T_A = -40$ to $+105\text{ }^{\circ}\text{C}$ (7 suffix versions)	10	kcycles
t_{RET}	Data retention	1 kcycle ⁽²⁾ at $T_A = 85\text{ }^{\circ}\text{C}$	30	Years
		1 kcycle ⁽²⁾ at $T_A = 105\text{ }^{\circ}\text{C}$	10	
		10 kcycle ⁽²⁾ at $T_A = 55\text{ }^{\circ}\text{C}$	20	

1. Data based on characterization results, not tested in production.

2. Cycling performed over the whole temperature range.

6.3.11 FSMC characteristics

Unless otherwise specified, the parameters given in [Table 45](#) to [Table 60](#) for the FSMC interface are derived from tests performed under the ambient temperature, f_{HCLK} frequency and V_{DD} supply voltage conditions summarized in [Table 19](#) with the following configuration:

- Output speed is set to $\text{OSPEEDRy}[1:0] = 11$
- Capacitive load $C = 30\text{ pF}$
- Measurement points are done at CMOS levels: $0.5V_{\text{DD}}$

Refer to [Section 6.3.15: I/O port characteristics](#) for more details on the input/output characteristics.

Table 51. Asynchronous multiplexed PSRAM/NOR write timings⁽¹⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	4THCLK-1	4THCLK+1	ns
$t_{v(NWE_NE)}$	FMC_NEx low to FMC_NWE low	THCLK	THCLK+0.5	
$t_{w(NWE)}$	FMC_NWE low time	2THCLK-0.5	2THCLK+1	
$t_{h(NE_NWE)}$	FMC_NWE high to FMC_NE high hold time	THCLK-0.5	-	
$t_{v(A_NE)}$	FMC_NEx low to FMC_A valid	-	5	
$t_{v(NADV_NE)}$	FMC_NEx low to FMC_NADV low	1	2.5	
$t_{w(NADV)}$	FMC_NADV low time	THCLK-2	THCLK+2	
$t_{h(AD_NADV)}$	FMC_AD(address) valid hold time after FMC_NADV high	THCLK-2	-	
$t_{h(A_NWE)}$	Address hold time after FMC_NWE high	THCLK-1	-	
$t_{h(BL_NWE)}$	FMC_BL hold time after FMC_NWE high	THCLK-0.5	-	
$t_{v(BL_NE)}$	FMC_NEx low to FMC_BL valid	-	1	
$t_{v(Data_NADV)}$	FMC_NADV high to Data valid	-	THCLK + 3.5	
$t_{h(Data_NWE)}$	Data hold time after FMC_NWE high	THCLK + 0.5	-	

1. Based on characterization, not tested in production.

Table 52. Asynchronous multiplexed PSRAM/NOR write-NWAIT timings⁽¹⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	9THCLK	9THCLK+0.5	ns
$t_{w(NWE)}$	FMC_NWE low time	6THCLK	6THCLK+2	
$t_{su(NWAIT_NE)}$	FMC_NWAIT valid before FMC_NEx high	5THCLK+6	-	
$t_{h(NE_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	5THCLK-5	-	

1. Based on characterization, not tested in production.

Synchronous waveforms and timings

[Figure 24](#) and [Figure 27](#) present the synchronous waveforms and [Table 53](#) to [Table 56](#) provide the corresponding timings. The results shown in these tables are obtained with the following FSMC configuration:

- BurstAccessMode = FMC_BurstAccessMode_Enable;
- MemoryType = FMC_MemoryType_CRAM;
- WriteBurst = FMC_WriteBurst_Enable;
- CLKDivision = 1;
- DataLatency = 2 for NOR Flash; DataLatency = 0 for PSRAM

In all timing tables, the THCLK is the HCLK clock period (with maximum FMC_CLK = 36 MHz).

Table 55. Synchronous non-multiplexed NOR/PSRAM read timings⁽¹⁾ (continued)

Symbol	Parameter	Min	Max	Unit
$t_{h(CLKH-DV)}$	FMC_D[15:0] valid data after FMC_CLK high	5	-	ns
$t_{su(NWAIT-CLKH)}$	FMC_NWAIT valid before FMC_CLK high	2	-	
$t_{h(CLKH-NWAIT)}$	FMC_NWAIT valid after FMC_CLK high	4	-	

1. Based on characterization, not tested in production.

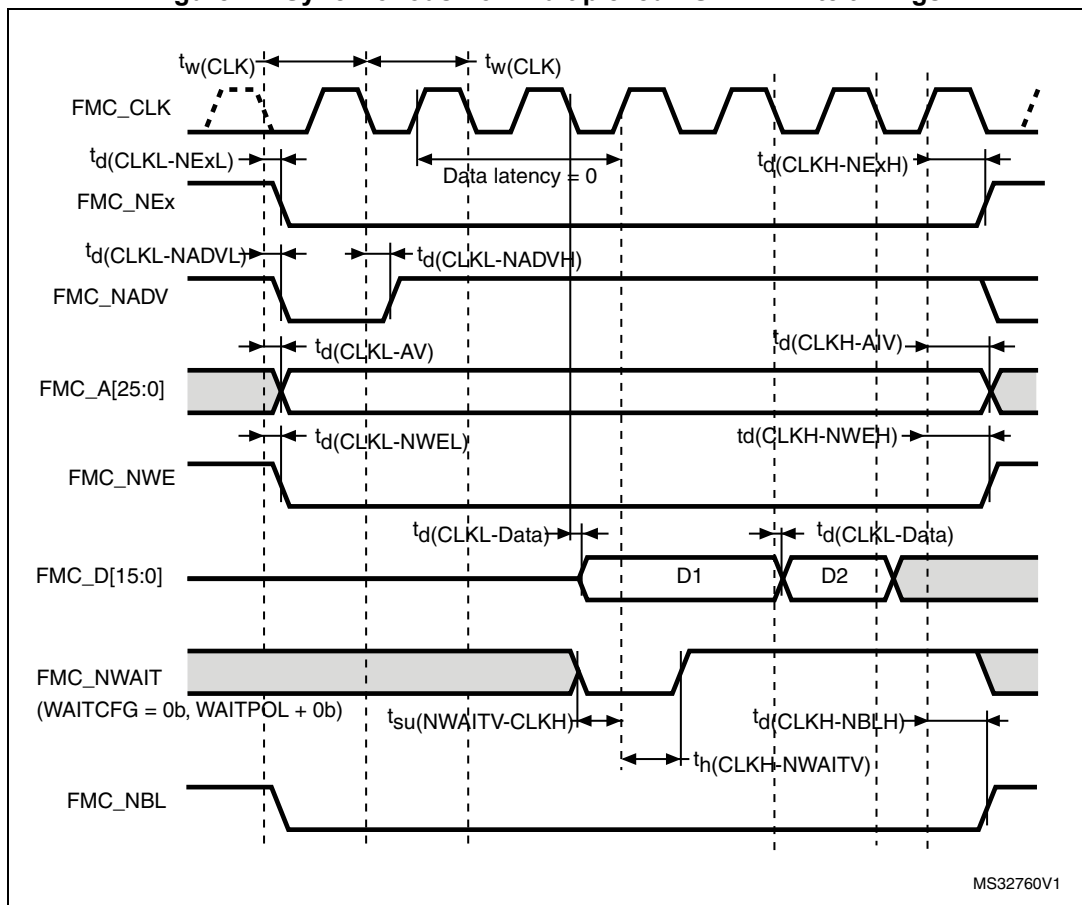
Figure 27. Synchronous non-multiplexed PSRAM write timings

Table 73. I2C analog filter characteristics⁽¹⁾

Symbol	Parameter	Min	Max	Unit
t_{AF}	Pulse width of spikes that are suppressed by the analog filter	50	260	ns

1. Guaranteed by design, not tested in production.

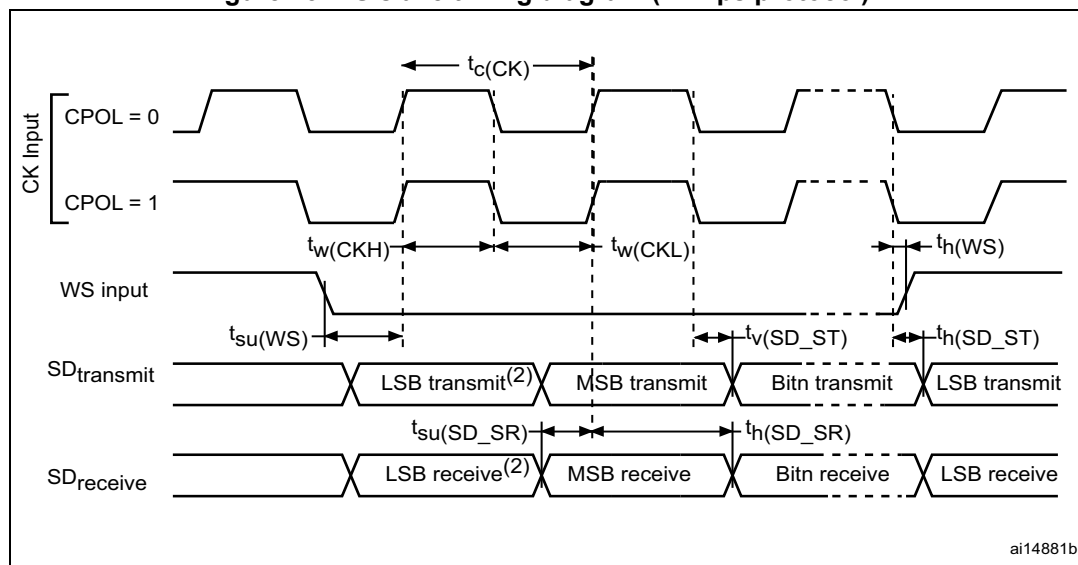
SPI/I²S characteristics

Unless otherwise specified, the parameters given in [Table 74](#) for SPI or in [Table 75](#) for I²S are derived from tests performed under ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in [Table 19](#).

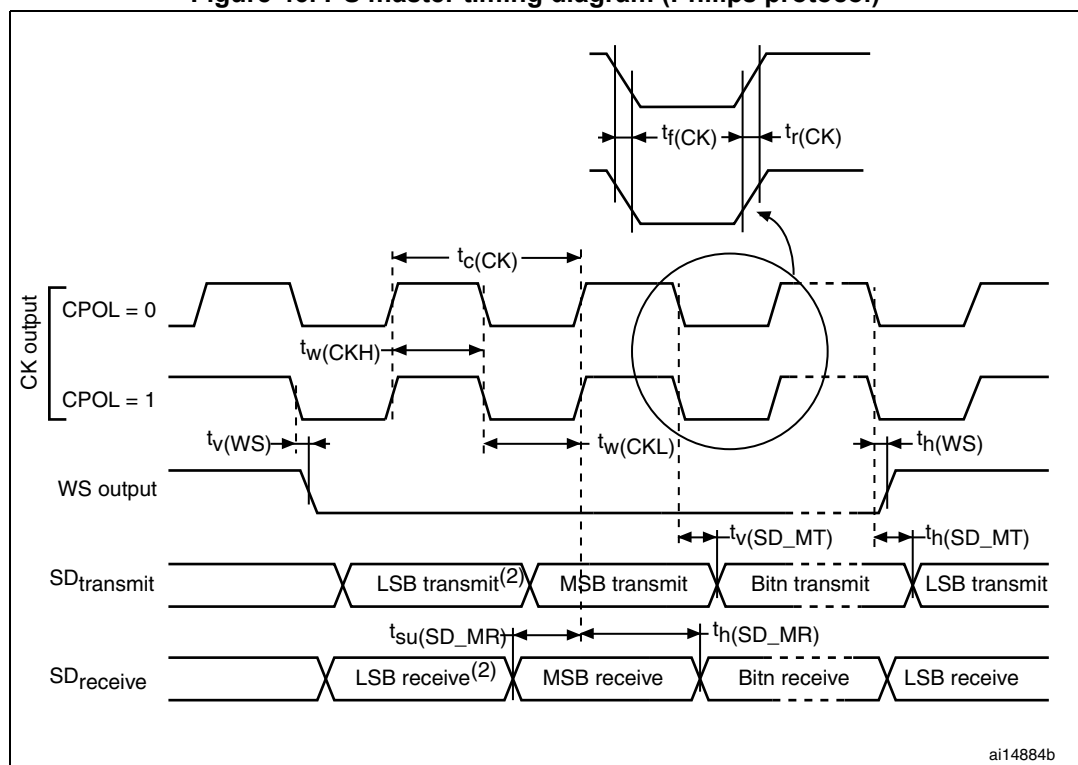
Refer to [Section 6.3.15: I/O port characteristics](#) for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO for SPI and WS, CK, SD for I²S).

Table 74. SPI characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ.	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode 2.7 V < V_{DD} < 3.6 V, SPI1/4	-	-	24	MHz
		Master mode 2 V < V_{DD} < 3.6 V, SPI1/2/3/4			18	
		Slave mode 2 V < V_{DD} < 3.6 V, SPI1/4			24	
		Slave mode 2 V < V_{DD} < 3.6 V, SPI1/2/3/4			18	
		Slave mode transmitter/full duplex 2 V < V_{DD} < 3.6 V, SPI1/2/3/4			16.5 ⁽²⁾	
		Slave mode transmitter/full duplex 2.7 V < V_{DD} < 3.6 V, SPI1/4			22.5 ⁽²⁾⁾	-
Duty _(SCK)	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%
$t_{su(NSS)}$	NSS setup time	Slave mode, SPI presc = 2	4* T_{pclk}	-	-	
$t_h(NSS)$	NSS hold time	Slave mode, SPI presc = 2	2* T_{pclk}	-	-	
$t_w(SCKH)$ $t_w(SCKL)$	SCK high and low time	Master mode	$T_{pclk}-2$	T_{pclk}	$T_{pclk}+2$	
$t_{su(MI)}$	Data input setup time	Master mode	3	-	-	
$t_{su(SI)}$		Slave mode	3	-	-	
$t_h(MI)$	Data input hold time	Master mode	6.5	-	-	
$t_h(SI)$		Slave mode	4.5	-	-	
$t_a(SO)$	Data output access time	Slave mode	10	-	30	
$t_{dis(SO)}$	Data output disable time	Slave mode	8	-	7	

Figure 45. I²S slave timing diagram (Philips protocol)⁽¹⁾

1. Measurement points are done at 0.5V_{DD} and with external C_L=30 pF.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Figure 46. I²S master timing diagram (Philips protocol)⁽¹⁾

1. Measurement points are done at 0.5V_{DD} and with external C_L=30 pF.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

USB characteristics

Table 76. USB startup time

Symbol	Parameter	Max	Unit
$t_{\text{STARTUP}}^{(1)}$	USB transceiver startup time	1	μs

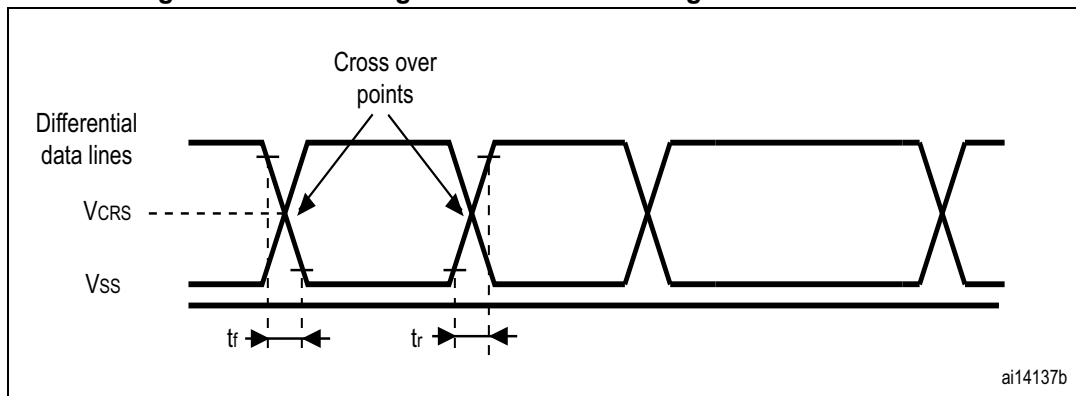
1. Guaranteed by design, not tested in production.

Table 77. USB DC electrical characteristics

Symbol	Parameter	Conditions	Min. ⁽¹⁾	Max. ⁽¹⁾	Unit
Input levels					
V _{DD}	USB operating voltage ⁽²⁾	-	3.0 ⁽³⁾	3.6	V
V _{DI} ⁽⁴⁾	Differential input sensitivity	I(USB_DP, USB_DM)	0.2	-	V
V _{CM} ⁽⁴⁾	Differential common mode range	Includes V _{DI} range	0.8	2.5	
V _{SE} ⁽⁴⁾	Single ended receiver threshold	-	1.3	2.0	
Output levels					
V _{OL}	Static output level low	R _L of 1.5 kΩ to 3.6 V ⁽⁵⁾	-	0.3	V
V _{OH}	Static output level high	R _L of 15 kΩ to V _{SS} ⁽⁵⁾	2.8	3.6	

- All the voltages are measured from the local ground potential.
- To be compliant with the USB 2.0 full-speed electrical specification, the USB_DP (D+) pin should be pulled up with a 1.5 k Ω resistor to a 3.0-to-3.6 V voltage range.
- The STM32F302xD/E USB functionality is ensured down to 2.7 V but not the full USB electrical characteristics which are degraded in the 2.7-to-3.0 V V_{DD} voltage range.
- Guaranteed by design, not tested in production.
- R_{L} is the load connected on the USB drivers.

Figure 47. USB timings: definition of data signal rise and fall time

Table 78. USB: full-speed electrical characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Driver characteristics						
t_r	Rise time ⁽²⁾	$C_{\text{L}} = 50 \text{ pF}$	4	-	20	ns
t_f	Fall time ⁽²⁾	$C_{\text{L}} = 50 \text{ pF}$	4	-	20	ns

Table 81. ADC accuracy - limited test conditions, 100-/144-pin packages ⁽¹⁾⁽²⁾ (continued)

Symbol	Parameter	Conditions			Min (3)	Typ	Max (3)	Unit
SNR ⁽⁴⁾	Signal-to-noise ratio	ADC clock freq. ≤ 72 MHz Sampling freq ≤ 5 Msps V _{DDA} = V _{REF+} = 3.3 V 25°C 100-pin/144-pin package	Single ended	Fast channel 5.1 Ms	66	67	-	dB
				Slow channel 4.8 Ms	66	67	-	
			Differential	Fast channel 5.1 Ms	69	70	-	
				Slow channel 4.8 Ms	69	70	-	
THD ⁽⁴⁾	Total harmonic distortion		Single ended	Fast channel 5.1 Ms	-	-76	-76	
				Slow channel 4.8 Ms	-	-76	-76	
			Differential	Fast channel 5.1 Ms	-	-80	-80	
				Slow channel 4.8 Ms	-	-80	-80	

1. ADC DC accuracy values are measured after internal calibration.
2. ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current. Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in [Section 6.3.15](#) does not affect the ADC accuracy.
3. Data based on characterization results, not tested in production.
4. Value measured with a -0.5 dB full scale 50 kHz sine wave input signal.

Table 82. ADC accuracy, 100-pin/144-pin packages ⁽¹⁾⁽²⁾⁽³⁾

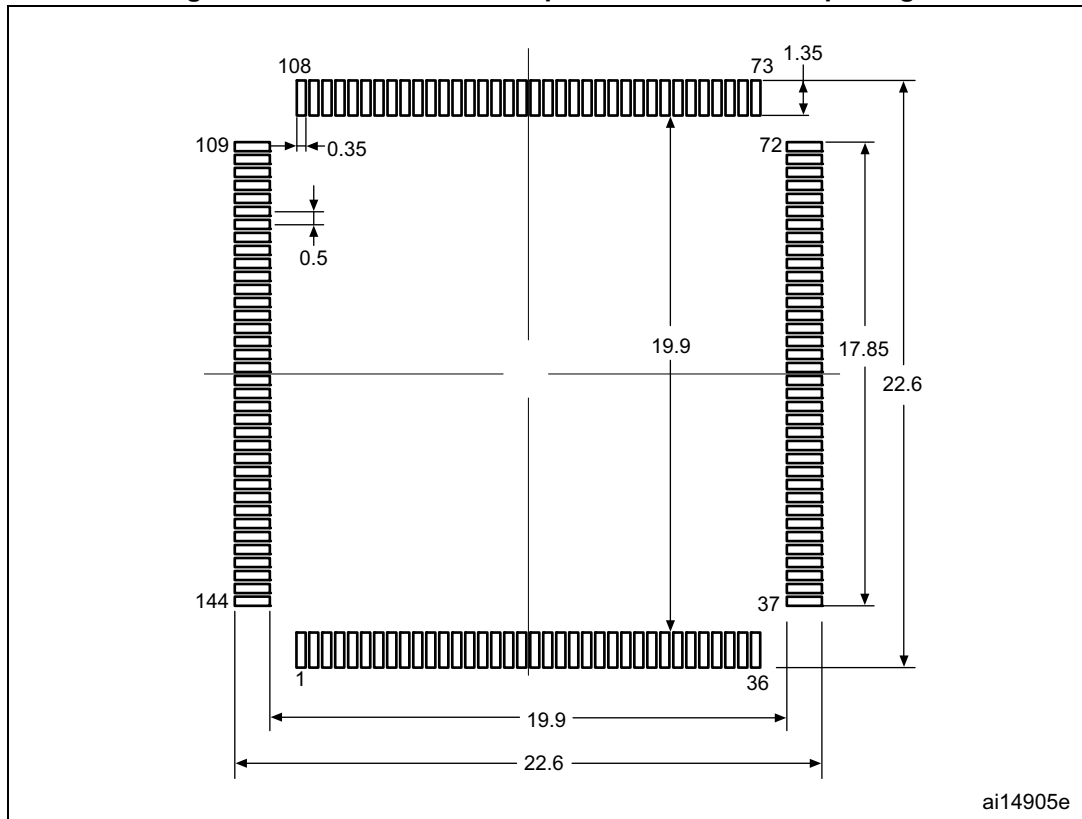
Symbol	Parameter	Conditions			Min ⁽⁴⁾	Max ⁽⁴⁾	Unit
ET	Total unadjusted error	ADC clock freq. ≤ 72 MHz, Sampling freq. ≤ 5 Msps 2.0 V ≤ V _{DDA} , V _{REF+} ≤ 3.6 V 100-pin/144-pin package	Single Ended	Fast channel 5.1 Ms	-	±6.5	LSB
				Slow channel 4.8 Ms	-	±6.5	
			Differential	Fast channel 5.1 Ms	-	±4	
				Slow channel 4.8 Ms	-	±4	
EO	Offset error		Single Ended	Fast channel 5.1 Ms	-	±3	
				Slow channel 4.8 Ms	-	±3	
			Differential	Fast channel 5.1 Ms	-	±2	
				Slow channel 4.8 Ms	-	±2	
EG	Gain error		Single Ended	Fast channel 5.1 Ms	-	±6	
				Slow channel 4.8 Ms	-	±6	
			Differential	Fast channel 5.1 Ms	-	±3	
				Slow channel 4.8 Ms	-	±3	
ED	Differential linearity error		Single Ended	Fast channel 5.1 Ms	-	±1.5	
				Slow channel 4.8 Ms	-	±1.5	
			Differential	Fast channel 5.1 Ms	-	±1.5	
				Slow channel 4.8 Ms	-	±1.5	

Table 84. ADC accuracy, 64-pin packages⁽¹⁾⁽²⁾⁽³⁾ (continued)

Symbol	Parameter	Conditions			Min ⁽⁴⁾	Max ⁽⁴⁾	Unit
EL	Integral linearity error	ADC clock freq. ≤ 72 MHz, Sampling freq ≤ 5 Msps, 2.0 V ≤ V _{DDA} ≤ 3.6 V 64-pin package	Single ended	Fast channel 5.1 Ms	-	±3	LSB
				Slow channel 4.8 Ms	-	±3.5	
			Differential	Fast channel 5.1 Ms	-	±2	
				Slow channel 4.8 Ms	-	±2.5	
ENOB ⁽⁵⁾	Effective number of bits		Single ended	Fast channel 5.1 Ms	10.4	-	bits
				Slow channel 4.8 Ms	10.4	-	
			Differential	Fast channel 5.1 Ms	10.8	-	
				Slow channel 4.8 Ms	10.8	-	
SINAD ⁽⁵⁾	Signal-to-noise and distortion ratio	Single ended	Fast channel 5.1 Ms	64	-	dB	
			Slow channel 4.8 Ms	63	-		
		Differential	Fast channel 5.1 Ms	67	-		
			Slow channel 4.8 Ms	67	-		
SNR ⁽⁵⁾	Signal-to-noise ratio	Single ended	Fast channel 5.1 Ms	64	-	dB	
			Slow channel 4.8 Ms	64	-		
		Differential	Fast channel 5.1 Ms	67	-		
			Slow channel 4.8 Ms	67	-		
THD ⁽⁵⁾	Total harmonic distortion	Single ended	Fast channel 5.1 Ms	-	-75	dB	
			Slow channel 4.8 Ms	-	-75		
		Differential	Fast channel 5.1 Ms	-	-79		
			Slow channel 4.8 Ms	-	-78		

1. ADC DC accuracy values are measured after internal calibration.
2. ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current. Any positive injection current within the limits specified for I_{INJ(PIN)} and ΣI_{INJ(PIN)} in [Section 6.3.15](#) does not affect the ADC accuracy.
3. Better performance may be achieved in restricted V_{DDA}, frequency and temperature ranges.
4. Data based on characterization results, not tested in production.
5. Value measured with a -0.5 dB full scale 50 kHz sine wave input signal.

Figure 55. Recommended footprint for the LQFP144 package

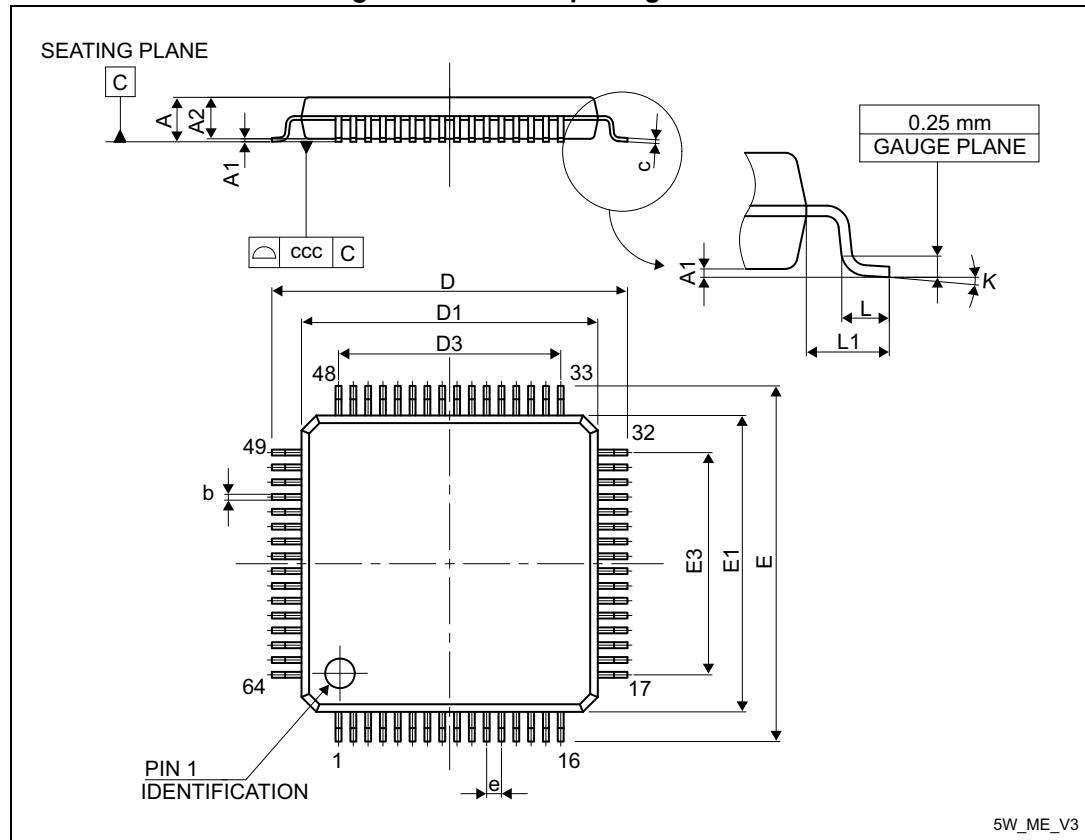


1. Drawing is not to scale.
2. Dimensions are expressed in millimeters.

7.6 LQFP64 package information

LQFP64 is a 64-pin, 10 x 10 mm low-profile quad flat package.

Figure 66. LQFP64 package outline



1. Drawing is not to scale.

Table 98. LQFP64 package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	-	12.000	-	-	0.4724	-
D1	-	10.000	-	-	0.3937	-
D3	-	7.500	-	-	0.2953	-
E	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-